

Image

PATENT



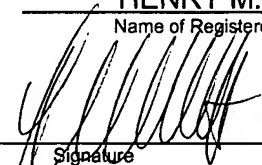
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Docket No.: WOLFF-4

In re Application of:)
THOMAS WOLFF)
Appl. No.: 10/693,771)
Filed: October 24, 2003)
For: METHOD AND DEVICE FOR PHOTO-)
ELECTRONICALLY ETCHING A)
SEMICONDUCTOR SAMPLE,)
ESPECIALLY GALLIUM NITRIDE)

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450", on November 19, 2003 .	
(Date)	
HENRY M. FEIEREISEN	
Name of Registered Representative	
	11-19-2003
Signature	Date of Signature

S I R:

In accordance with 37 C.F.R. 1.56, applicant wishes to call the attention of the Examiner to the following references A) to C) which were cited in the instant specification. Applicant does not admit that any of the cited documents constitutes prior art against the pending application.

	Country:	Patent or Appl. No:	Patentee or Applicant:	Issue or Filing Date:
A)		Adesida et al.: "Dry and Wet Etching for Group III ..."		00-00-1999
B)		Youtsey et al.: "Smooth n-type GaN surfaces by .."		00-00-1998
C)		Notten et al.: "Etching of III-V Semiconductors"		00-00-1991

Copies of these references are submitted herewith along with form PTO-1449. The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

☒ This Information Disclosure Statement is filed within three months of the filing date of a national application other than a continued prosecution application under 1.53(d), so that no fee under 37 C.F.R. §1.97 is due.

☐ This Information Disclosure Statement is filed within three months of the date of entry of the national stage as set forth in 1.491 in an international application, so that no fee under 37 C.F.R. §1.97 is due.

☐ This Information Disclosure Statement is filed before the mailing of a first Office Action on the merits, so that no fee under 37 C.F.R. §1.97 is due.

☐ This Information Disclosure Statement is filed before the mailing of a first Office Action after the filing of a request for continued examination under §1.114, so that no fee under 37 C.F.R. §1.97 is due.

☐ This Information Disclosure Statement is filed after the issuance of a first office but before issuance of a final action under §1.113, or a notice of allowance under §1.311.

☐ This Information Disclosure Statement is submitted after the mailing of a final action or a notice of allowance, but before payment of the issue fee.

☐ The undersigned submits the following statement requesting consideration of this statement:

The undersigned hereby states:

☐ That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement;

☐ That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the statement after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in §1.56(c) more than three months prior to the filing of the information disclosure statement.

☐ The fee of \$180.00 set forth in 1.17(p).

☐ The Commissioner is hereby authorized to charge the fee as set forth in 1.17(p), and any additional fees which may be required, or credit any overpayment to Deposit Account No. 06-0502.

☐ The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment to Deposit Account No. 06-0502.

The above-identified application discloses and claims an invention patentable over this prior art.

Entry of the references above set forth into the file of the above application is believed to be in order and is respectfully requested.

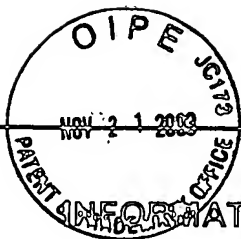
The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment to Deposit Account No. 06-0502.

Respectfully submitted

By: 

Henry M. Feiereisen
Agent for Applicant
Reg. No. 31,084

Date: November 19, 2003
350 Fifth Avenue
Suite 4714
New York, N.Y. 10118
(212) 244-5500
HMF:be



Form PTO-1449

U.S. Department of Commerce
Patent and Trademark Office

INFORMATION DISCLOSURE CITATION

Attorney's Docket No. WOLFF-4	Applicant Thomas Wolff	Appl. No. 10/693,771
Filing Date October 24, 2003	Group	Examiner

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date, if appropriate

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Adesida et al.: "Dry and Wet Etching for Group III-Nitrides", 1999
	Youtsey et al.: "Smooth n-type GaN surfaces by photoenhanced wet etching", 1998
	Notten et al.: "Etching of III-V Semiconductors", 1991

Examiner:

Date considered:

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.